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Physical analysis workflow in context of GaN HEMT failure analysis.

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This talk reports the workflow developed to characterize AlGaIn/GaN high electron mobility transistors (HEMTs) gate defects in order to link physical defects with their electrical signature. Taking into account the particularities of GaN technologies such as the thin active layer and the interface quality importance, we correlated different technics ranging from «Slice&View» to Transmission Electron Microscopy (TEM) and EDS-EELS mapping to identify defects with their electrical signature.

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